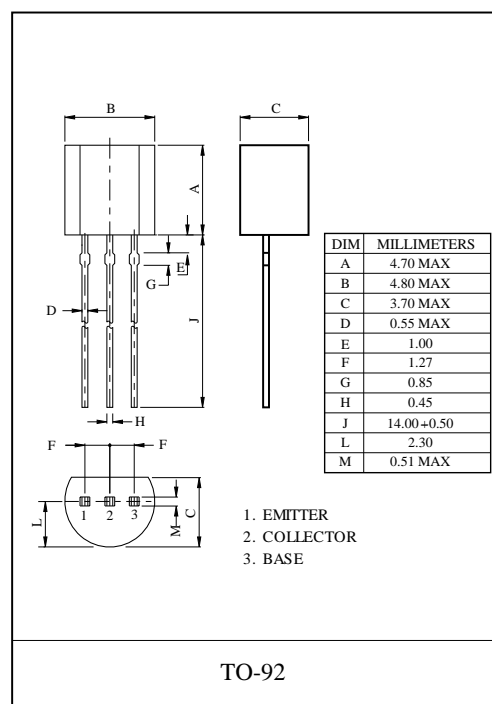


FEATURES

- TO-92 PNP Transistor

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-150	mA
P _D	Collector Power Dissipation	600	mW
T _j	Junction Temperature	125	°C
T _{stg}	Storage Temperature	-55-125	°C



ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -100μA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -0.1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -50V, I _E =0			-0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} = -50V, I _B =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} = -6V, I _C = -2mA	70		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -100mA, I _B = -10mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -100mA, I _B = -10mA			-1.1	V
Transition frequency	f _T	V _{CE} = -10 V, I _C = -1mA f =30MHz	80			MHz
Collector Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			7	pF
Noise Figure	NF	V _{CE} = -6 V, I _C = -0.1mA, f =1KHz, R _G =10K			6	dB

CLASSIFICATION OF h_{FE}

Rank	O	Y	GR
Range	70-140	120-240	200-400

